

Shottky barrier diode

RB400D

●Application

Low current rectification

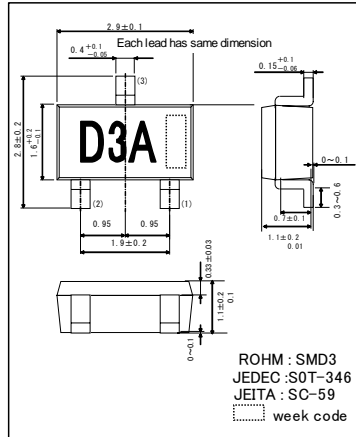
●Features

- 1) Small mold type. (SMD3)
- 2) Low Ir
- 3) High reliability.

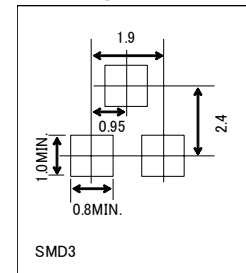
●Structure

Silicon epitaxial planer

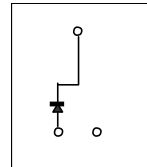
●External dimensions (Unit : mm)



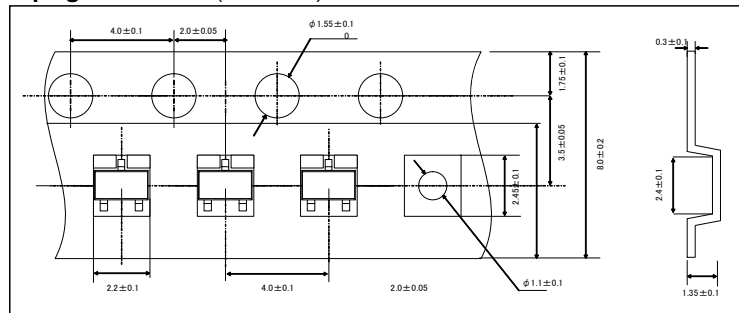
●Lead size figure (Unit : mm)



●Structure



●Taping dimensions (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	40	V
Reverse voltage (DC)	V_R	40	V
Average rectified forward voltage (*1)	I_o	500	mA
Forward current surge peak (60Hz·1cyc) (*1)	I_{FSM}	3	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

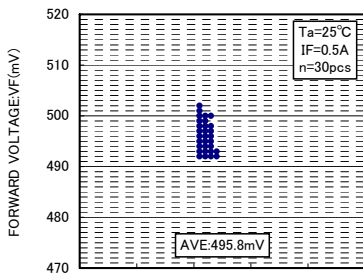
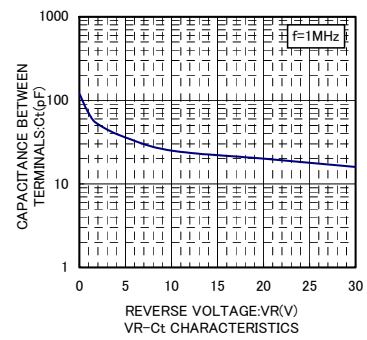
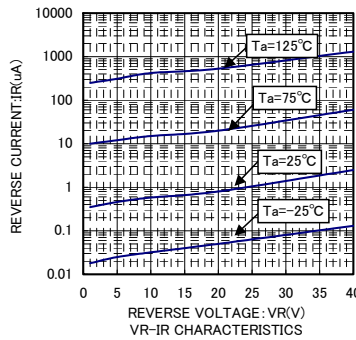
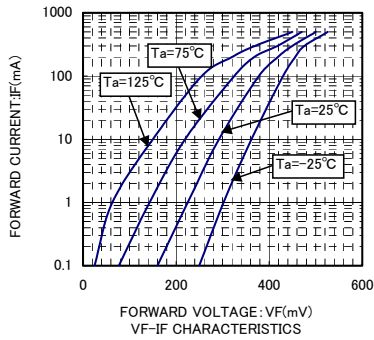
(*1) Rating of per diode

●Electrical characteristics (Ta=25°C)

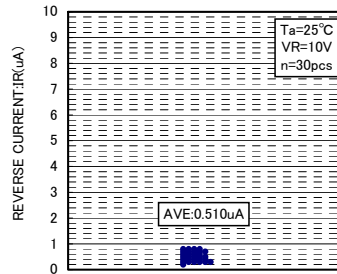
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.55	V	$I_F=500mA$
Reverse current	I_{R1}	-	-	30	μA	$V_R=10V$
	I_{R2}	-	-	50	μA	$V_R=30V$
Capacitance between terminals	Ct1	-	125	-	pF	$V_R=0V, f=1MHz$
	Ct2	-	20	-	pF	$V_R=10V, f=1MHz$

Diodes

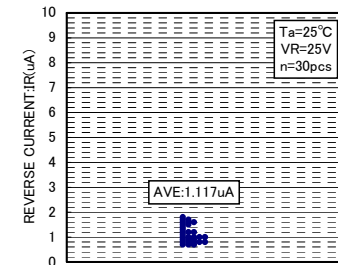
●Electrical characteristic curves (Ta=25°C)



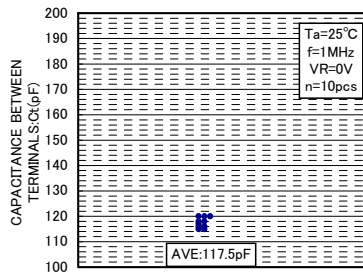
VF DISPERSION MAP



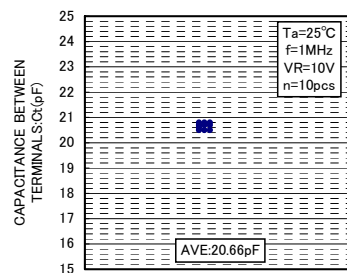
IR DISPERSION MAP



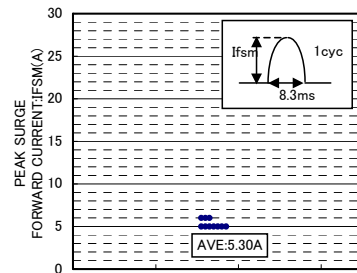
IR DISPERSION MAP



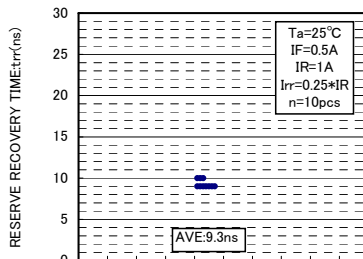
Ct DISPERSION MAP



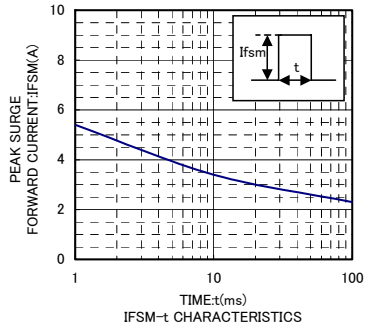
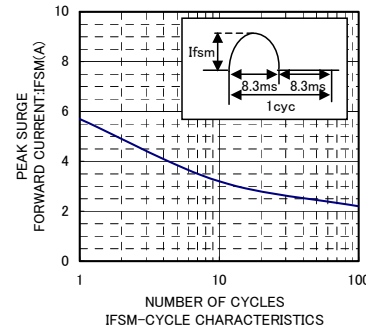
Ct DISPERSION MAP



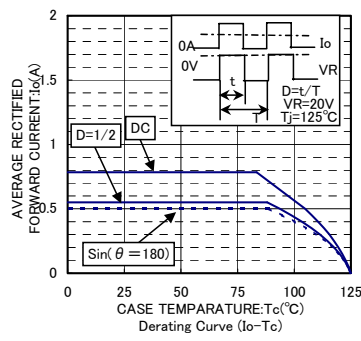
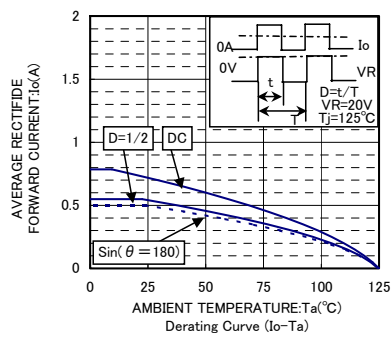
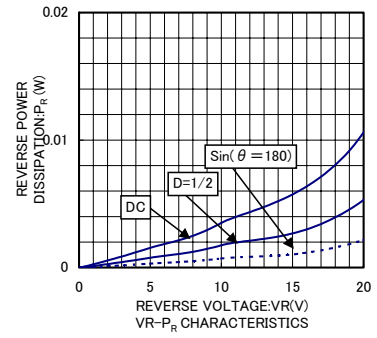
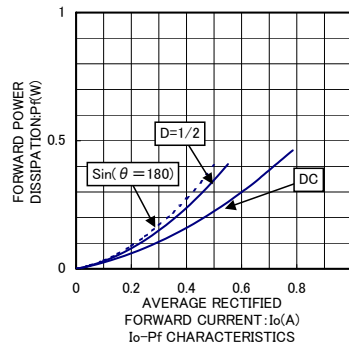
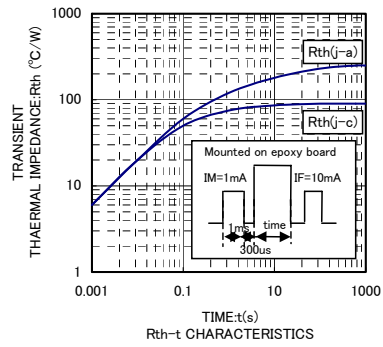
IFSM DISRESION MAP



trr DISPERSION MAP



Diodes



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